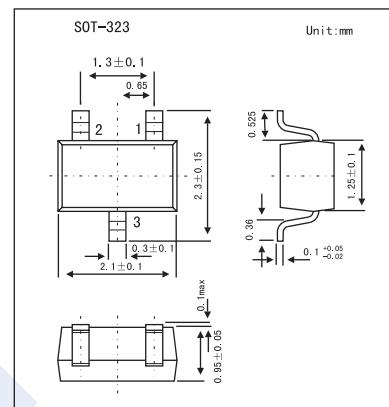
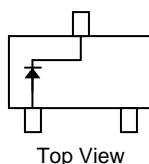


Surface Mount Schottky Barrier Diode

1SS401

■ Features

- Low forward voltage: $V_F(3) = 0.38 \text{ V(Typ)}$
- Low reverse current: $I_R = 50 \mu\text{A}$
- Small total capacitance: $C_T = 46 \text{ pF(Typ)}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Maximum (peak) reverse voltage	V_{RM}	25	V
Reverse voltage	V_R	20	V
Maximum (peak) forward current	I_{FM}	700	mA
Average forward current	I_o	300	mA
Power dissipation	P	100	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +125	$^\circ\text{C}$

(*) Unit rating. Total rating = Unit rating $\times 0.7$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward voltage	$V_F(1)$	$I_F = 1 \text{ mA}$		0.16		V
	$V_F(2)$	$I_F = 10 \text{ mA}$		0.22		
	$V_F(3)$	$I_F = 300 \text{ mA}$		0.38	0.45	
Reverse Current	I_R	$V_R = 20 \text{ V}$			50	μA
Total capacitance	C_T	$V_R = 0, f = 1.0 \text{ MHz}$		46		pF

■ Marking

Marking	D9
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Surface Mount Schottky Barrier Diode

1SS401

■ Typical Characteristics

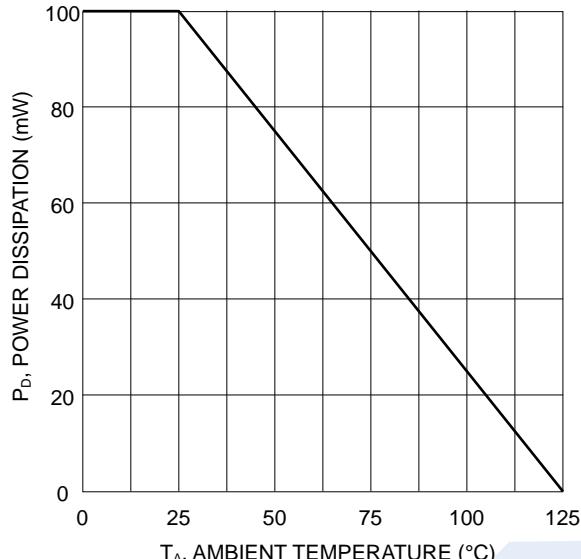


Fig. 1 Power Derating Curve

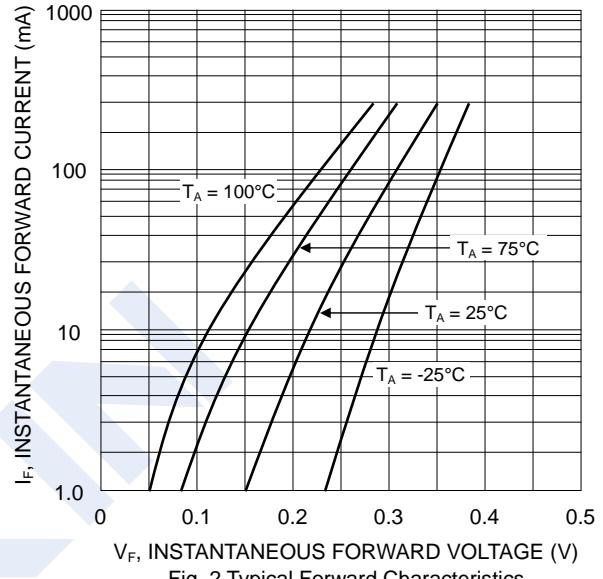


Fig. 2 Typical Forward Characteristics

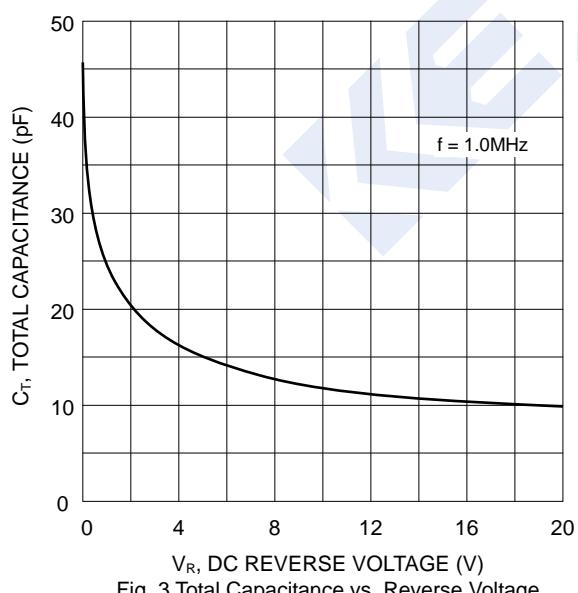


Fig. 3 Total Capacitance vs. Reverse Voltage

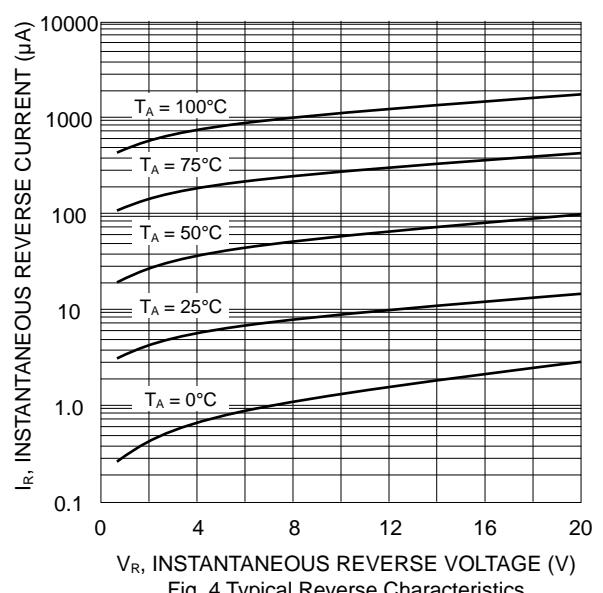


Fig. 4 Typical Reverse Characteristics